

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

Device	V _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
Q1	30V	1.5Ω @ $V_{GS} = 4.5V$	350mA
Qi	307	2.0Ω @ $V_{GS} = 2.5V$	SSUTIA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

- Low On-Resistance: R_{DS(ON)}
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

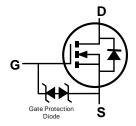
- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208[®]
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

SOT523

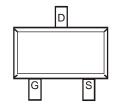




Top View



Equivalent Circuit



Top View Pin Out Configuration

Ordering Information (Note 4)

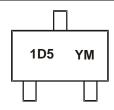
Part Number	Case	Packaging
DMN31D6UT-7	SOT523	3,000/Tape & Reel
DMN31D6UT-13	SOT523	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



Marking Information



1D5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014)M = Month (ex: 9 = September)

Date Code Key

Year	2014	2	2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		E	F		G	Н		1
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Au	g Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	±12	V
Drain Current (Note 6)	Continuous	I _D	350	mA
Pulsed Drain Current (Note 6)		I _{DM}	800	mA

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	210	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	593	°C/W
mermai Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	542	C/VV
Total Power Dissipation (Note 6)		P_{D}	320	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	398	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	363	C/VV
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

Notes:

5. Device mounted on FR-4 PCB, with minimum recommended pad layout 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.

DMN31D6UT Document number: DS38191 Rev. 1 - 2

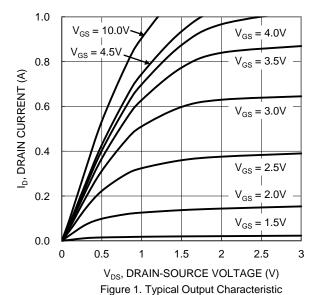


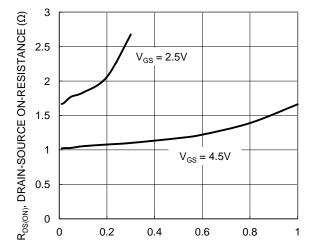
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
DFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current @T _C = +25°0	C I _{DSS}	_	_	100	nA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	1.1	1.5	Ω	$V_{GS} = 4.5V, I_D = 100mA$	
Static Dialii-Source Off-Nesistance	R _{DS(ON)}	_	1.6	2.0	1 12	$V_{GS} = 2.5V, I_D = 50mA$	
Diode Forward Voltage	V_{SD}	_	0.6	1.0	V	$V_{GS} = 0V$, $I_S = 10mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		_	13.6	_	pF		
Output Capacitance		_	3.1	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	_	2.2	_	pF	1.500112	
Total Gate Charge	Q_g	_	0.35	_	nC	45)	
Gate-Source Charge	Q_{gs}	_	0.06	_	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$ $V_{DS} = 15V,$	
Gate-Drain Charge		_	0.19	_	nC	-1D = 20011IA	
Turn-On Delay Time	t _{D(ON)}	_	3.3	_	ns		
Turn-On Rise Time		_	2.3	_	ns	$V_{DD} = 15V, V_{GS} = 4.5V,$	
Turn-Off Delay Time		_	7.4	_	ns	$R_G = 2\Omega$, $I_D = 200$ mA	
Turn-Off Fall Time		_	4.4	_	ns		

7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

0.6

8.0

0.4

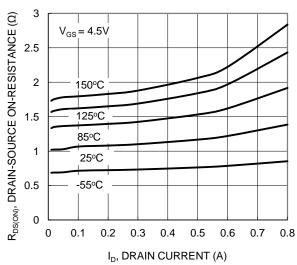


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

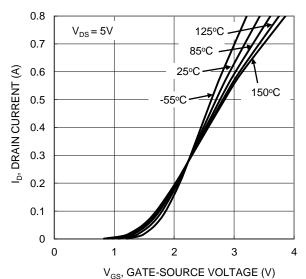


Figure 2. Typical Transfer Characteristic

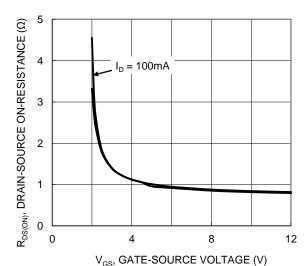


Figure 4. Typical Transfer Characteristic

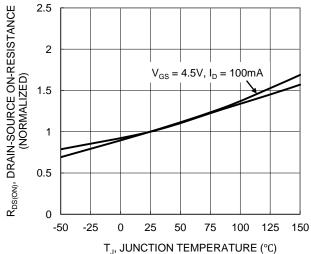


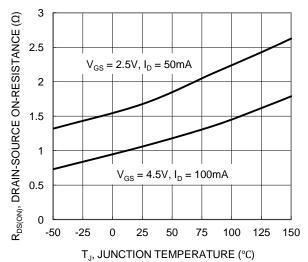
Figure 6. On-Resistance Variation with Junction Temperature

0

0

0.2





Figue 7. On-Resistance Variation with Junction Temperature

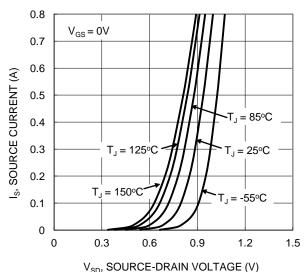


Figure 9. Diode Forward Voltage vs. Current

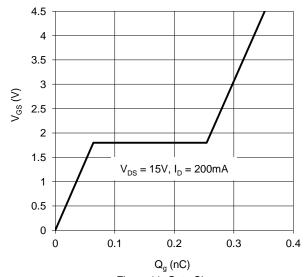


Figure 11. Gate Charge

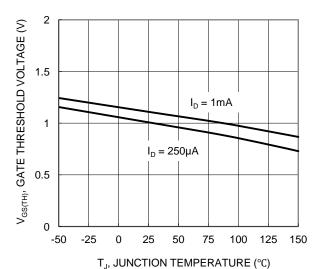


Figure 8. Gate Threshold Variation vs. Junction Temperature

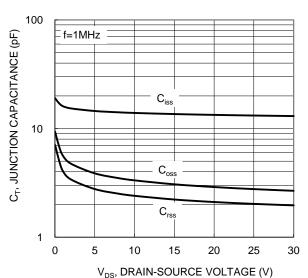


Figure 10. Typical Junction Capacitance

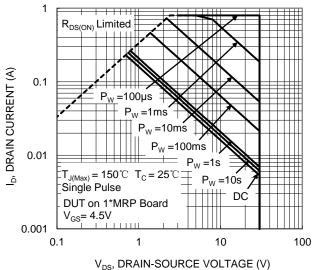


Figure 12. SOA, Safe Operation Area



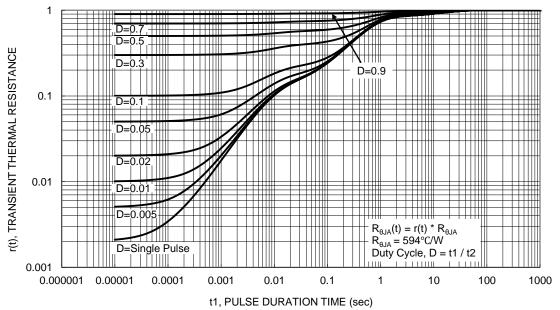


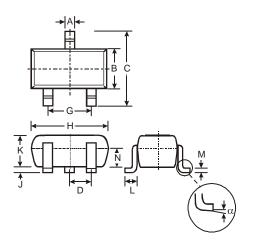
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT523

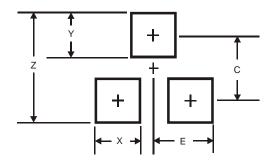


SOT523							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
C	1.45	1.75	1.60				
D			0.50				
G	0.90	1.10	1.00				
H	1.50	1.70	1.60				
J	0.00	0.10	0.05				
K	0.60	0.80	0.75				
L	0.10	0.30	0.22				
M	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	0°	8°	_				
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT523



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Υ	0.51
С	1.3
E	0.7



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2015, Diodes Incorporated

www.diodes.com

8 of 8 DMN31D6UT Document number: DS38191 Rev. 1 - 2 Downloaded From Oneyac.com

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))